

359-609/610

BUS14  
BUS14A

## SILICON DIFFUSED POWER TRANSISTORS

High-voltage, high-speed, glass-passivated n-p-n power transistors in a TO-3 envelope, intended for use in converters, inverters, switching regulators, motor control systems etc.

## QUICK REFERENCE DATA

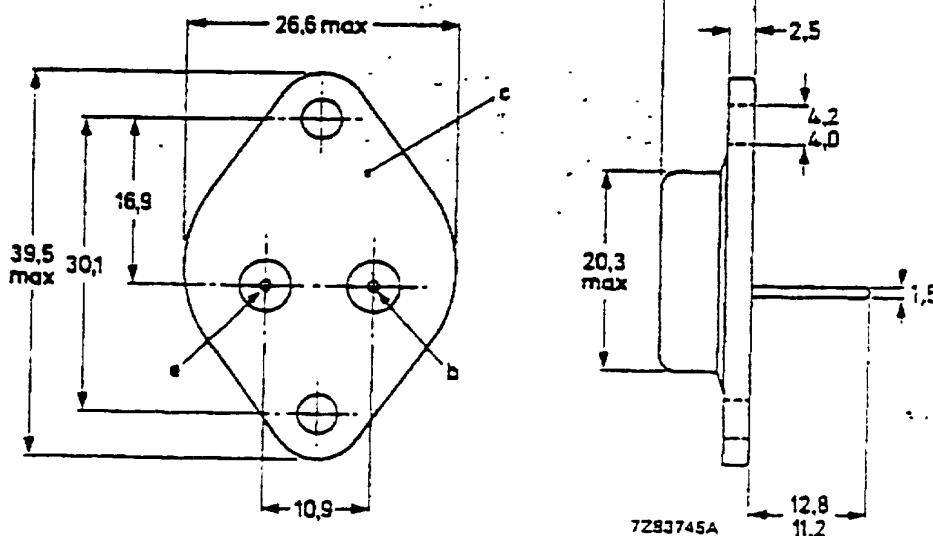
	BUS14		BUS14A
Collector-emitter voltage ( $V_{BE} = 0$ , peak value)	$V_{CESM}$	max. 950	1000 V
Collector-emitter voltage (open base)	$V_{CEO}$	max. 400	450 V
Collector current (d.c.)	$I_C$	max. 30	A
Collector current (peak value) $t_p < 2$ ms	$I_{CM}$	max. 50	A
Total power dissipation up to $T_{mb} = 25$ °C	$P_{tot}$	max. 250	W
Collector-emitter saturation voltage $I_C = 20$ A; $I_B = 4$ A	$V_{CEsat}$	< 1,5	— V
$I_C = 16$ A; $I_B = 3,2$ A	$V_{CEsat}$	< —	1,5 V
Fall time (resistive load) $I_{Con} = 20$ A; $I_{Bon} = -I_{Boff} = 4$ A	$t_f$	< 0,8	— $\mu$ s
$I_{Con} = 16$ A; $I_{Bon} = -I_{Boff} = 3,2$ A	$t_f$	< —	0,8 $\mu$ s

## MECHANICAL DATA

Dimensions in mm

Fig. 1 TO-3.

Collector connected to case.



See also chapters Mounting instructions and Accessories.

January 1983

181

BUS14  
BUS14A

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

		BUS14	BUS14A
Collector-emitter voltage ( $V_{BE} = 0$ , peak value)	$V_{CESM}$	max. 850	1000 V
Collector-emitter voltage (open base)	$V_{CEO}$	max. 400	450 V
Collector current (d.c.)	$I_C$	max. 30	A
Collector current (peak value); $t_p < 2$ ms	$I_{CM}$	max. 50	A
Base current (d.c.)	$I_B$	max. 6	A
Base current (peak value); $t_p < 2$ ms	$I_{BM}$	max. 10	A
Total power dissipation up to $T_{mb} = 25$ °C	$P_{tot}$	max. 250	W
Storage temperature	$T_{stg}$	-65 to +200	°C
Junction temperature	$T_j$	max. 200	°C

THERMAL RESISTANCE

From junction to mounting base	$R_{th\ j-mb}$	=	0,7	K/W
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CHARACTERISTICS

$T_j = 25$  °C unless otherwise specified

Collector cut-off current \*

$V_{CE} = V_{CESMmax}; V_{BE} = 0$	$I_{CES}$	<	1	mA
$V_{CE} = V_{CESMmax}; V_{BE} = 0; T_j = 125$ °C	$I_{CES}$	<	5	mA

Emitter cut-off current

$I_C = 0; V_{EB} = 9$ V	$I_{EBO}$	<	10	mA
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Saturation voltages

	BUS14	BUS14A	
$I_C = 20$ A; $I_B = 4$ A	$V_{CEsat}$	< 1,5	- V
$I_C = 16$ A; $I_B = 3,2$ A	$V_{CEsat}$	< -	1,5 V
$I_C = 20$ A; $I_B = 4$ A	$V_{BESat}$	< 1,7	- V
$I_C = 16$ A; $I_B = 3,2$ A	$V_{BESat}$	< -	1,7 V

Collector-emitter sustaining voltage

$I_C = 100$ mA; $I_{Boff} = 0$ ; $L = 25$ mH	$V_{CEO}sust$	> 400	450 V
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\* Measured with a half sine-wave voltage (curve tracer).

Silicon diffused power transistors

BUS14  
BUS14A

## CHARACTERISTICS (continued)

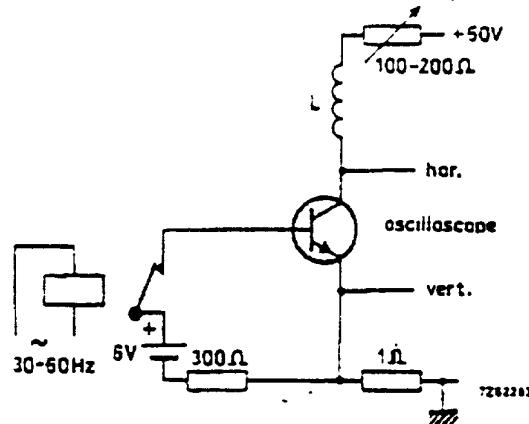
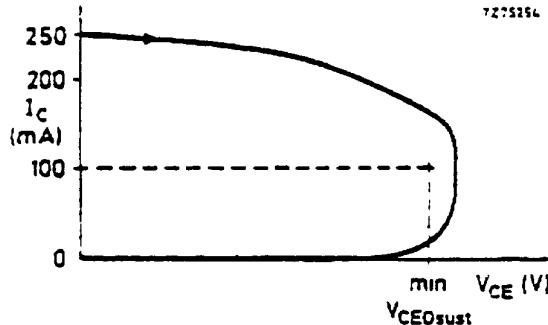


Fig. 2 Oscilloscope display for sustaining voltage.

Fig. 3 Test circuit for  $V_{CEO,sust}$ .

## Switching times resistive load (Figs 4 and 5)

$$I_{Con} = 20 \text{ A}; I_{Bon} = -I_{Boff} = 4 \text{ A}$$

Turn-on time

	BUS14	BUS14A
$t_{on}$	< 1	- $\mu\text{s}$

Turn-off: Storage time  
Fall time

$t_s$	< 4	- $\mu\text{s}$
$t_f$	< 0,8	- $\mu\text{s}$

$$I_{Con} = 16 \text{ A}; I_{Bon} = -I_{Boff} = 3,2 \text{ A}$$

Turn-on time

$t_{on}$	<	1 $\mu\text{s}$
$t_s$	<	4 $\mu\text{s}$
$t_f$	<	0,8 $\mu\text{s}$

Turn-off: Storage time  
Fall time

## Switching times inductive load (Figs 6 and 7)

$$I_{Con} = 20 \text{ A}; I_B = 4 \text{ A}$$

Turn-off: Storage time

$t_s$	typ. 2,8	- $\mu\text{s}$
$t_s$	< 3,6	- $\mu\text{s}$
$t_f$	typ. 80	- ns
$t_f$	< 150	- ns

Fall time

$$I_{Con} = 20 \text{ A}; I_B = 4 \text{ A}; T_j = 100^\circ\text{C}$$

Turn-off: Storage time

$t_s$	typ. 3,1	- $\mu\text{s}$
$t_s$	< 4,0	- $\mu\text{s}$
$t_f$	typ. 140	- ns
$t_f$	< 300	- ns

Fall time

## Switching times inductive load (Figs 6 and 7)

$$I_{Con} = 16 \text{ A}; I_B = 3,2 \text{ A}$$

Turn-off: Storage time

$t_s$	typ. -	28 $\mu\text{s}$
$t_s$	< -	3,6 $\mu\text{s}$
$t_f$	typ. -	80 ns
$t_f$	< -	150 ns

Fall time

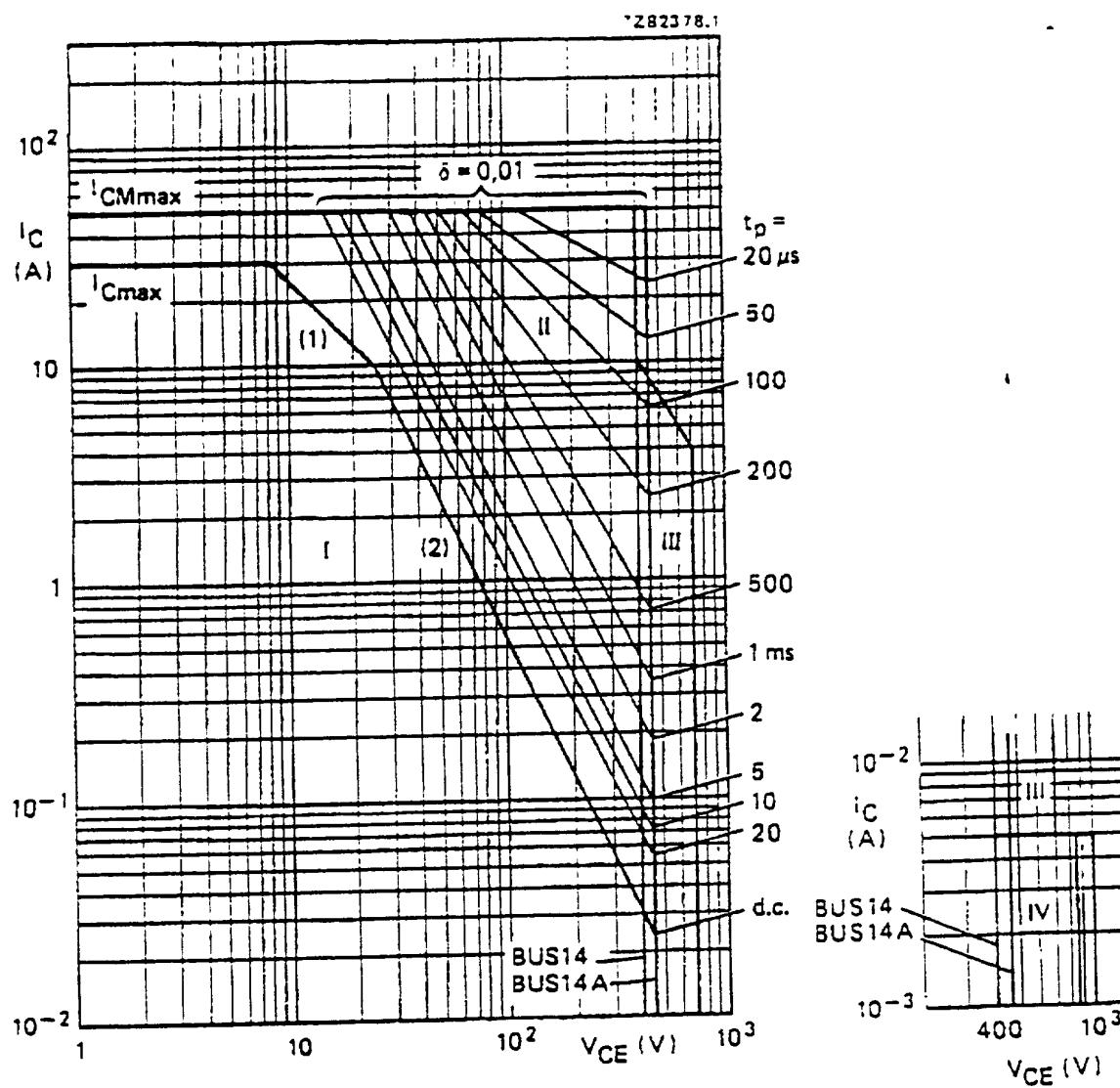
$$I_{Con} = 16 \text{ A}; I_B = 3,2 \text{ A}; T_j = 100^\circ\text{C}$$

Turn-off: Storage time

$t_s$	typ. -	3,1 $\mu\text{s}$
$t_s$	< -	4,0 $\mu\text{s}$
$t_f$	typ. -	140 ns
$t_f$	< -	300 ns

Fall time

Silicon diffused power transistors

BUS14  
BUS14AFig. 8 Safe Operating Area at  $T_{mb} \leq 25^\circ\text{C}$ .

- (1)  $P_{tot\ max}$  and  $P_{peak\ max}$  lines.
- (2) Second-breakdown limits (independent of temperature).
- I Region of permissible d.c. operation
- II Permissible extension for repetitive pulse operation
- III Area of permissible operation during turn-on in single transistor converters, provided  $R_{BE} \leq 100 \Omega$  and  $t_p \leq 0.6 \mu s$
- IV Repetitive pulse operation in this region is permissible provided  $V_{BE} \leq 0$  and  $t_p \leq 2 \text{ ms}$ .

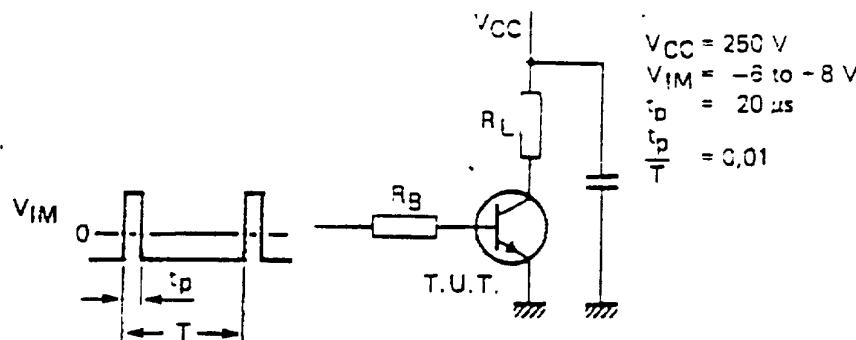


Fig. 4 Test circuit resistive load.

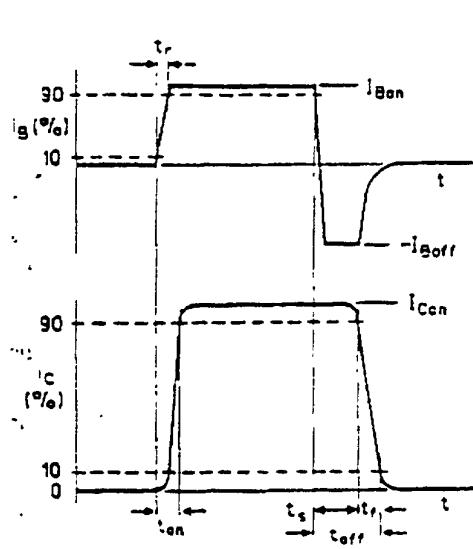


Fig. 5 Switching times waveforms with resistive load.

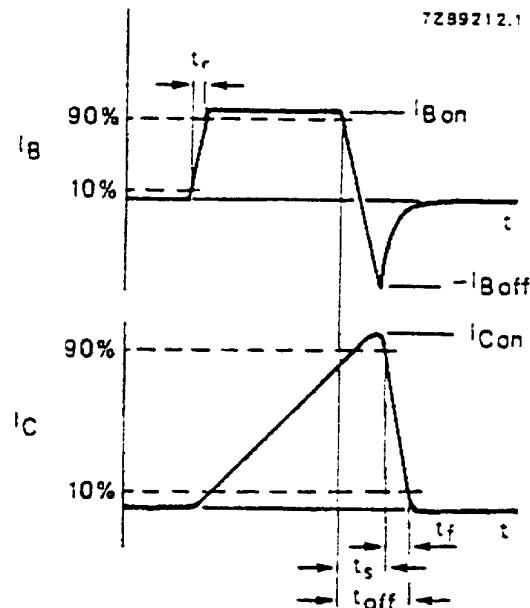


Fig. 6 Switching times waveforms with inductive load.

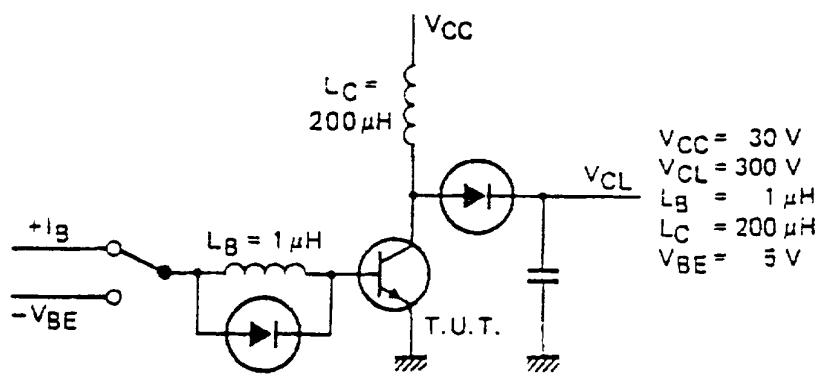


Fig. 7 Test circuit inductive load.

BUS14  
BUS14A



Fig. 9 Total power dissipation and second-breakdown current derating curve.

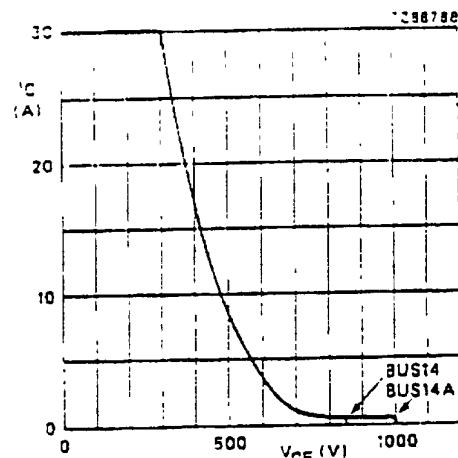


Fig. 10 Reverse bias SOAR.

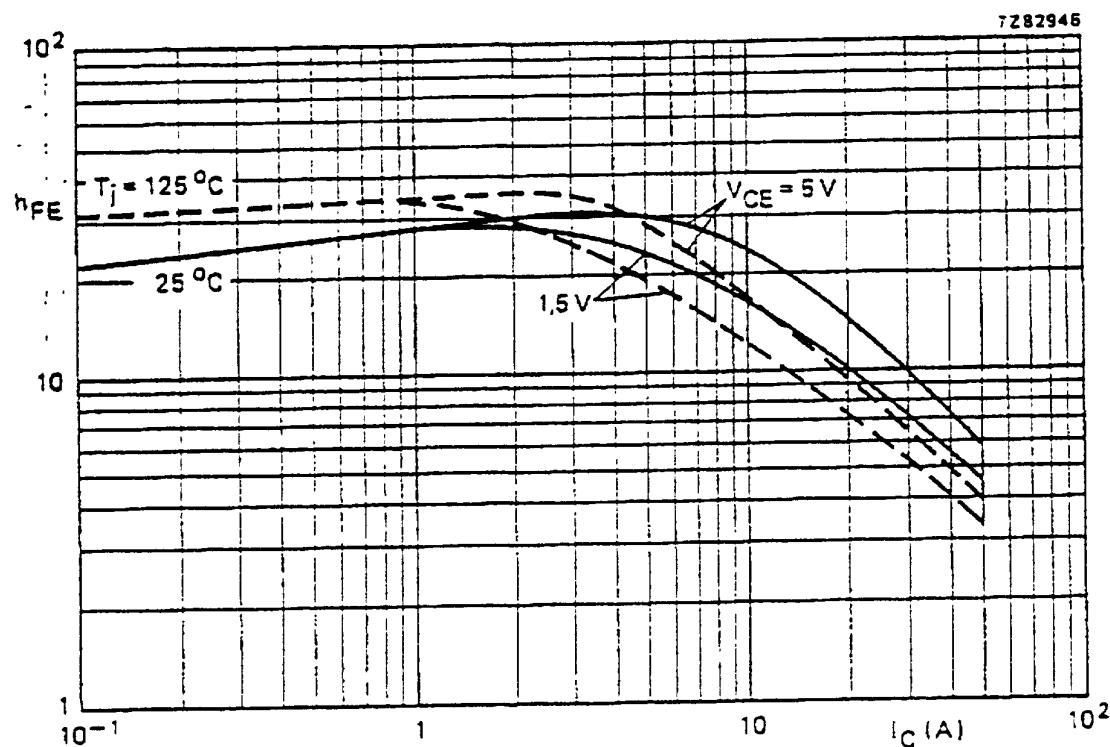


Fig. 11 Typical values d.c. current gain.

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BUS14  
BUS14A**APPLICATION INFORMATION**

Important design factors of SMPS circuits are the maximum power losses, heatsink requirements and base drive conditions of the switching transistor. The power losses are very dependent on the operating frequency, the maximum collector current amplitude and shape.

The operating frequency is mostly set between 15 and 50 kHz. The collector current shape varies from rectangular in a forward converter to sawtooth in a flyback converter.

Information on nominal base drive, optimum base inductance and maximum transistor dissipation applied in a forward converter is given in Figs 15, 16 and 17. In these figures  $I_{CM}$  represents the maximum repetitive peak collector current, which occurs during overload. The information is derived from limit-case transistors at a mounting base temperature of 100 °C under the following conditions (see also Fig. 15):

- collector current shape  $I_C1/I_{CM} = 0,9$
- duty factor  $t_D/T = 0,45$
- rate of rise of  $I_C$  during turn-on = 20 A/ $\mu$ s
- rate of rise of  $V_{CE}$  during turn-off = 1 kV/ $\mu$ s
- reverse drive voltage during turn-off = 5 V
- base current shape  $I_B1/I_{B(end)} = 1,5$

The required thermal resistance of the heatsink can be calculated from

$$R_{th\ mb-a} < \frac{100 - T_{amb}}{P_{tot}} \text{ K/W}$$

To ensure thermal stability the value of the ambient temperature  $T_{amb} > 40$  °C.

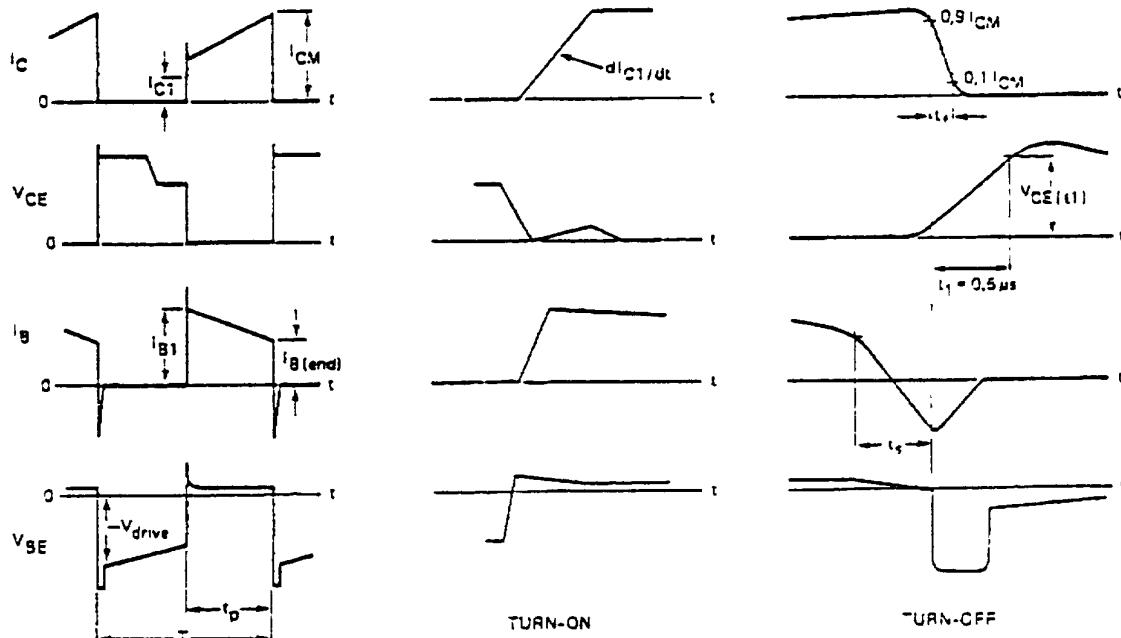
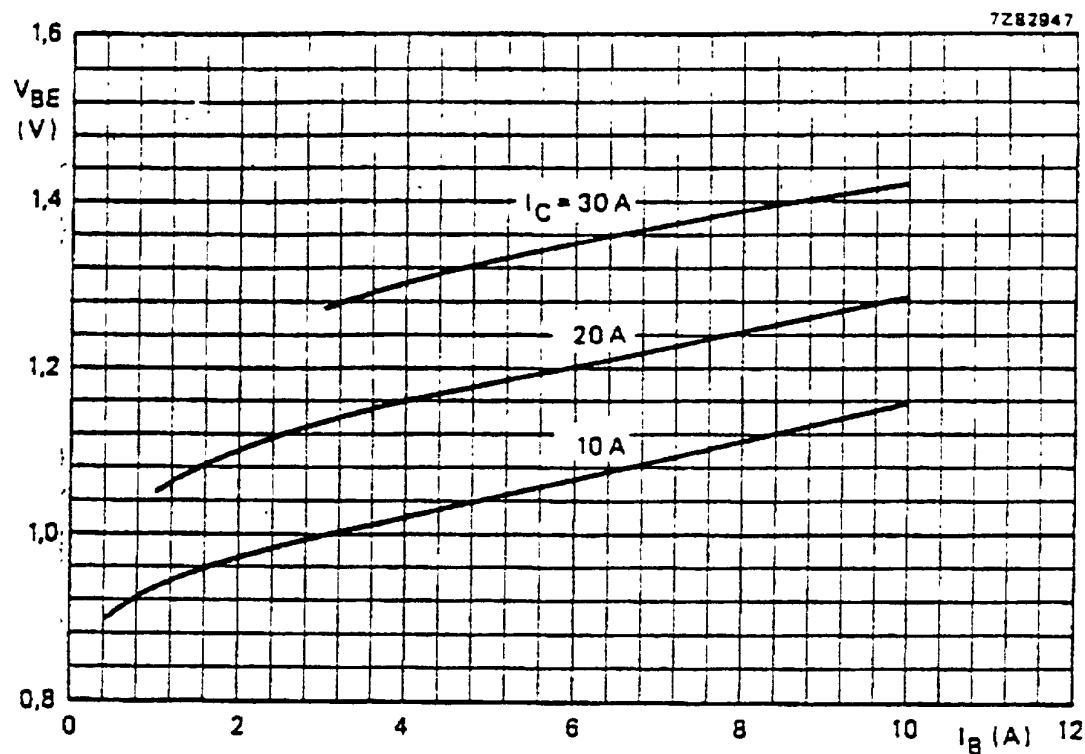


Fig. 15 Relevant waveforms of the switching transistor in a forward SMPS.

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BUS14  
BUS14AFig. 14 Typical values at  $T_j = 25\text{ }^\circ\text{C}$ .

188

January 1983

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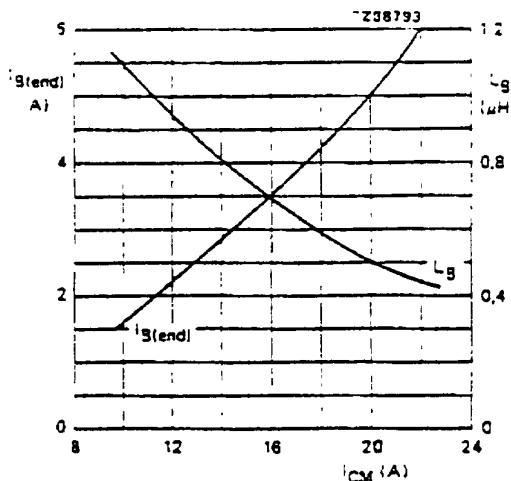


Fig. 16 Recommended nominal "end" value of the base current ( $I_{B(end)}$ ) and optimum base inductance ( $L_B$ ) at  $-V_{drive} = 5$  V versus maximum peak collector current.  $dI_B(end) = \pm 20\%$ .

For other values of  $-V_{drive}$  (3 V to 7 V) the related  $L_B$  is:

$$L_{Bnom} = \frac{(-V_{drive}) + 1}{6}$$

$L_{Bnom}$  is the value given in this graph.

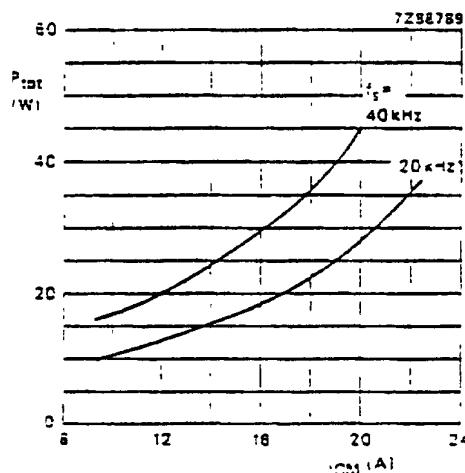


Fig. 17 Maximum transistor dissipation under worse-case operating condition versus maximum peak collector current.  $T_{mb} = 100$  °C;  $dI_B(end) = \pm 20\%$ .